

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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MAR 15 2004 JC88
PATENT & TRADEMARK OFFICE

In re Application of:)	Examiner: Unassigned
)	
Pravin K.Narwankar, et al.)	Art Unit: Unassigned
)	
Serial No. 10/772,893)	
)	
Filed: February 4, 2004)	
)	
For: Tailoring Nitrogen Profile In Silicon)	
Oxynitride Using Rapid Thermal)	
Annealing With Ammonia Under)	
Ultra-Low Pressure)	

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is a copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 together with copies of the documents cited on that form, except for copies not required to be submitted (e.g., copies of U.S. patents and U.S. published patent applications need not be enclosed for applications filed after June 30, 2003). It is respectfully requested that the cited documents be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

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has been made and is not to be construed as an admission that the information cited in this statement is material to patentability.

Pursuant to 37 C.F.R. § 1.97, this Information Disclosure Statement is being submitted under one of the following (as indicated by an "X" to the left of the appropriate paragraph):

X 37 C.F.R. §1.97(b).

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 A statement pursuant to 37 C.F.R. §1.97(e) or

 A check for \$180.00 for the fee under 37 C.F.R. § 1.17(p).

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If there are any additional charges, please charge Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP



Dated: March 10, 2004

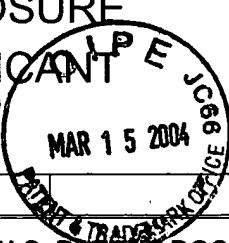
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)



Sheet		of		Attorney Docket Number	008209/USA/FEP/GCM/RKK
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U.S. PATENT DOCUMENTS					
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FOREIGN PATENT DOCUMENTS

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
		ITO, T., et al., "Direct Thermal Nitridation of Silicon Dioxide Films In Anhydrous Ammonia Gas," J. Electrochem Soc.: Solid-State and Technology/Optical Properties, Vol. 127, No. 9, September 1980, pages 2053-2057,	
		ITO, T., et al., "Retardation of Destructive Breakdown of SiO ₂ Films Annealed in Ammonia Gas," J. Electrochem Soc.: Solid-State and Technology/Ammonia Gas, Vol. 127, No. 10, September 1980, pages 2248-2251,	
		LEK, C. M., et al., "Impact of Decoupled Plasma Nitridation of Ultra-Thin Gate Oxide on the Performance of P-Channel MOSFETs," Institute of Physics Publishing, Semicond. Sci. Technol., Vol. 17, 2002, pages L25-L28.	

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*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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